



# A Broadband Zero-IF Down-Conversion Mixer in 130 nm SiGe BiCMOS for Beyond 5G Communication Systems in D-Band

Andreas Tsouchlos | 10.09.2024



#### **Overview**



Proposed Ideas

Own Simulations

#### **Overview**



Proposed Ideas

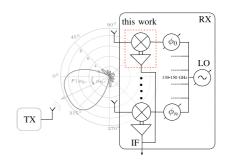
Own Simulations

#### **Proposed Design: Overview**

Paper by Maiwald, et al. [Mai+21]







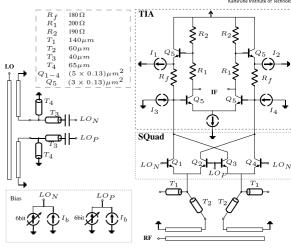
- High bandwidth, low power consumption, small size
- Applicable to electronic beam stearing for mm-Wave
- SiGe BiCMOS technology (B11HFC) from Infineon Technologies AG with  $f_{\rm t}/f_{\rm max}$  of  $250/370\,{\rm GHz}$

[Mai+21] T. Maiwald et al., "A Broadband Zero-IF Down-Conversion Mixer in 130 nm SiGe BiCMOS for Beyond 5G Communication Systems in D-Band", in IEEE Transactions on Circuits and Systems II: Express Briefs, vol. 68, no. 7, pp. 2277-2281, July 2021

### **Proposed Design: Mixer Core Cell**



- Usage of switching quad (SQuad) instead of conventional Gilbert cell for more voltage headroom
- Mixer loaded by modified Cherry-Hooper [сн63] transimpedance amplifier (ТІА)
- Transmission line based differential L-type matching networks for high bandwidth
- Signal fed using marchand baluns for high bandwidth

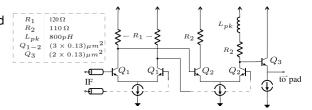


[CH63] E.M. Cherry and D.E. Hooper, "The design of wide-band transistor feedback amplifiers", *Proceedings of the Institution of Electrical Engineers*, vol. 110, pp. 375-389, February 1963

## **Proposed Design: IF Buffer**

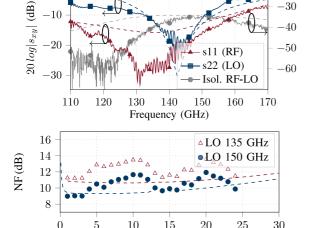


- Three-stages: two differential amplifier stages and an emitter follower
- Includes differential to single-ended conversion enabling dense chip-to-package transition
- Inductive peaking for bandwidth enhancement

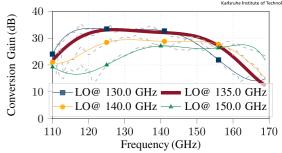


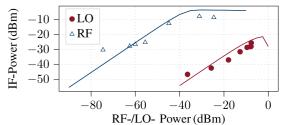
### Proposed Design: Simulation/Measurement Results





Frequency (GHz)





#### **Overview**



Proposed Ideas

Own Simulations

### **Design Steps**

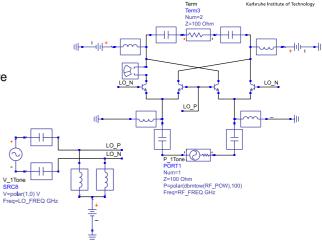


- Determination of operating point of individual stages
  - SQuad
  - TIA
  - Buffer
- Integration
  - SQuad & TIA
  - SQuad, TIA & Buffer
- **3** Further iterative optimization of parameters (e.g., determine LO power, increase buffer current for linearity, . . . )
- Matching of input and output

## **Operating Point: Switching Quad**

Karlsruhe Institute of Technology

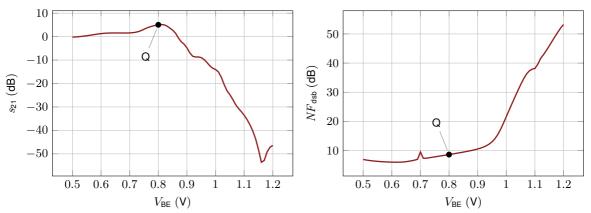
- Operation
  - Responsible for actual mixing
  - Multiplication of RF-signal with square wave
    - $\rightarrow$  generation of mixing products at IF-frequency and harmonics
- Determination of operating point
  - $\blacksquare$  Exact value of  $V_{CE}$  not crucial
  - V<sub>BE</sub>: Examination of s<sub>21</sub> of Large-signal s-parameter simulation and noise figure (analogous to [Mai+21])



[Mai+21] T. Maiwald et al., "A Broadband Zero-IF Down-Conversion Mixer in 130 nm SiGe BiCMOS for Beyond 5G Communication Systems in D-Band", in IEEE Transactions on Circuits and Systems II: Express Briefs, vol. 68, no. 7, pp. 2277-2281, July 2021

## **Operating Point: Switching Quad**



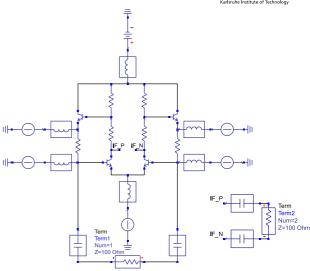


- Plotted for  $f_{LO} = 135 \, \text{GHz}, f_{RF} = 140 \, \text{GHz}$
- lacktriangle Double-sideband noise figure  $NF_{dsb}$  (direct conversion mixer)
- Chosen operating point:  $V_{BE} = 0.8 \, \text{V}$

## **Operating Point: Transimpedance Amplifier**

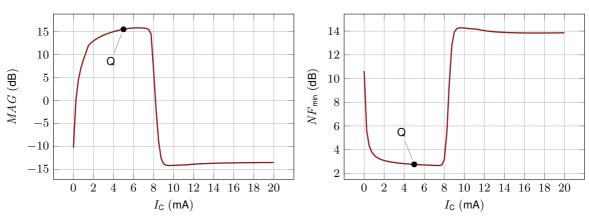


- Operation
  - Conversion of switched current to voltage, amplification
  - Modified Cherry-Hooper topology: decoupling of bandwidth and gain, modification for greater dynamic range
- Determination of operating point
  - Exact value of supply voltage not crucial
  - S-parameter simulation: Examination of maximum available gain (MAG) and minimum noise figure (NF<sub>min</sub>)
  - At this stage: only determination of operating point of bottom transistors



# **Operating Point: Transimpedance Amplifier**



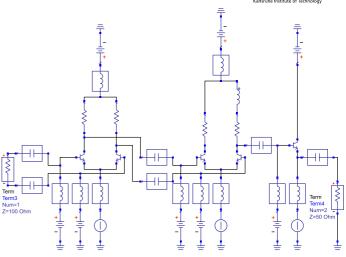


- Plotted for  $f_{\mathsf{IF}} = 20\,\mathsf{GHz}$
- Chosen operating point:  $I_C = 5 \text{ mA}$  (with multiplier of 10)

## **Operating Point: Buffer**

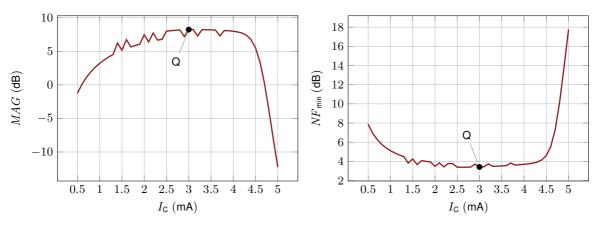


- Operation
  - Amplification of signal
  - Comprises three stages: two differential amplifiers and an emitter follower
- Determination of operating point
  - Exact value of supply voltage not crucial at this point
  - S-parameter simulation: Examination of MAG and  $NF_{min}$
  - Note: Adjustment with respect to linearity at the very end



## **Operating Point: Buffer**

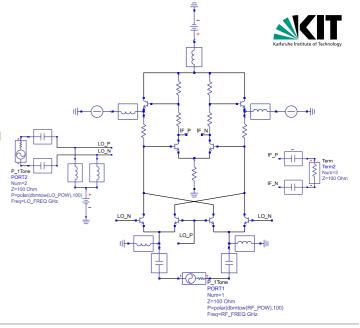




- Plotted for  $f_{\rm IF}=20\,{\rm GHz}$
- Chosen operating point:  $I_C = 3 \text{ mA}$

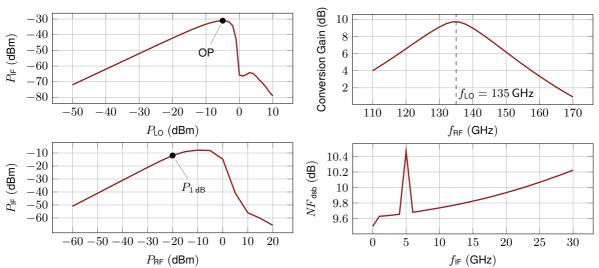
# Integration: SQuad & TIA

- DC coupling → Redesign of bias circuitry
- Supply voltage fixed to 2,5 V to not exceed breakdown voltage of transistors
- Examination using Harmonic-Balance simulation:
  - Conversion gain
  - $\blacksquare$  1 dB compression point ( $P_{1 \text{ dB}}$ )



#### Integration: SQuad & TIA

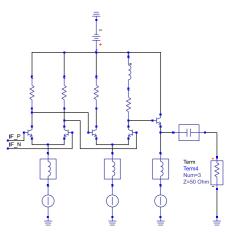




## Integration: SQuad, TIA & Buffer

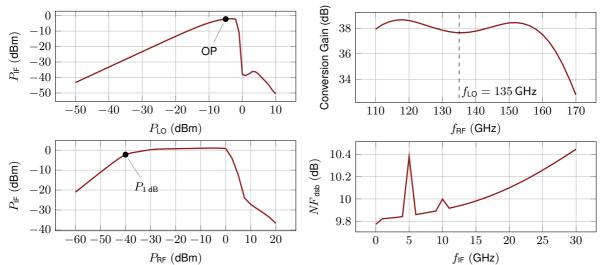


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  - Conversion gain
  - $\blacksquare 1 \, \mathsf{dB} \; \mathsf{compression} \; \mathsf{point} \; (P_{1 \, \mathsf{dB}})$

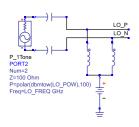


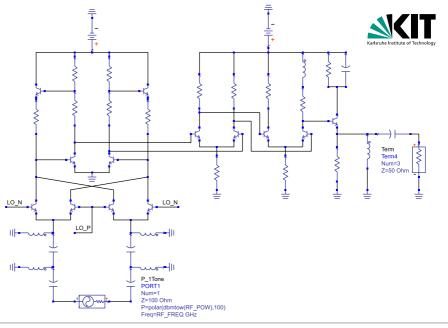
## Integration: SQuad, TIA & Buffer





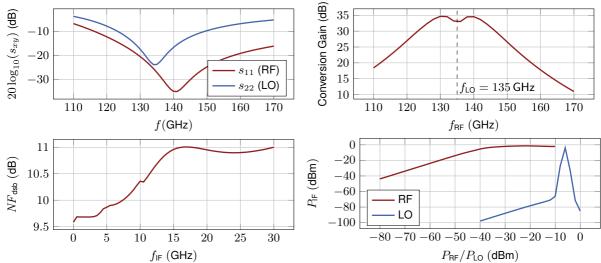
#### **Final Circuit**





#### **Final Circuit**





#### **Overview**



Proposed Ideas

Own Simulations



- General structure
  - Removal of  $g_m$  stage of Gilbert cell  $\rightarrow$  more voltage headroom
  - $\blacksquare$  High bandwidth TIA and inductive peaking  $\rightarrow$  high bandwidth
  - lacktriangle Differential to single-ended conversion o dense chip-to-package transition
- Own simulations
  - Better results to be expected (technology with higher  $f_t$ ,  $f_{max}$ , stability not considered)
  - Further investigation needed to determine whether unusual LO power behavior is problematic
  - Maybe better results by using current mirrors to set operating points of buffer instead of resistors
  - Maybe better results by replacement of discrete component matching networks by transmission line based ones
- Applications of this design
  - lacktriangle SiGe HBT technology integrable with CMOS ightarrow scalable, suitable for mixed-signal ICs
  - Ideal for electronic beam stearing in mm-Wave applications (because of small size, moderate noise figure)

#### Questions



Thank you for your attention!
Any questions?

